P27135.A02

Serial No.: 10/711,640

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Basanth JAGANNATHAN Group Art Unit: 2818

Appln. No. : 10/711,640 Examiner: Nguyen, Tram

Filed: September 29, 2004 Confirmation No: 5639

For : STRUCTURE AND LAYOUT OF A FET PRIME CELL

Commissioner for Patents
U.S. Patent and Trademark Office
Customer Service Window, Mail Stop Amendment
Randolph Building
401 Dulany Street
Alexandria, VA 22314

RESPONSE TO RESTRICTION AND ELECTION OF SPECIES REQUIREMENT AND AMENDMENT

Sir:

In response to the Office Action dated December 28, 2005, Applicants elect Group I, Species A, claims 14-20, without traverse. Please amend the above-identified application as follows:

A listing of the claims is set forth on pages 2-3.

Remarks begin on page 4.

If extensions of time are necessary to prevent abandonment of this application, then such extensions of time are hereby petitioned under 37 C.F.R. §1.136(a), and any fees required therefor (including fees for net addition of claims) are hereby authorized to be charged to Deposit Account No. 09-0458.

AMENDMENT TO THE CLAIMS

Please CANCEL claims 1-13 and 21-30

A copy of all pending claims and a status of the claims is provided below.

Claims 1-13. (canceled)

- 14. (original) A semiconductor device, comprising:
- a substrate;
- a source and a drain arranged within the substrate;
- a gate formed on the substrate between the source and drain; and
- a substrate contact formed within the substrate in electrical contact with the source.
- 15. (original) The semiconductor device of claim 14, further comprising the substrate contact being configured to shield the semiconductor device from electrical noise.
- 16. (original) The semiconductor device of claim 14, further comprising the substrate contact being in direct physical contact with the source of the semiconductor device.
- 17. (original) The semiconductor device of claim 14, wherein the substrate contact comprises a p+ region.
- 18. (original) The semiconductor device of claim 14, wherein the source comprises a source finger and the substrate contact abuts substantially all of one side of the source finger.

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19. (original) The semiconductor device of claim 18, comprising at least two source fingers arranged within the substrate, wherein the substrate contact abuts two of the at least two source fingers.

20. (original) The semiconductor device of claim 14, wherein the substrate contact comprises a p-type doped silicon tab contacting the source and a silicide layer arranged on top of the substrate contact.

Claims 21-30. (canceled)

REMARKS

Claims 14-20 are currently pending in the application. By this amendment, claims 1-13 and 21-30 are canceled. Applicants elect Group I, Species A, claims 14-20, without traverse.

Applicants request examination on the merits. The Examiner is invited to contact the undersigned at the telephone number listed below, if needed.

Respectfully submitted, Basanth JAGANNATHAN

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